

SPTECH Silicon NPN Power Transistor

2SC1403

DESCRIPTION

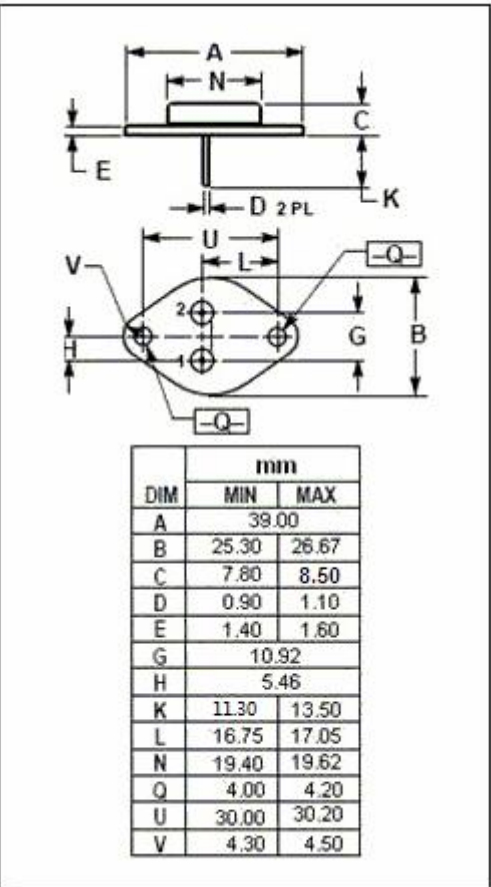
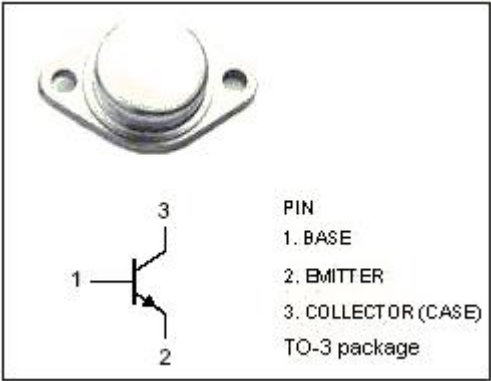
Wide area of safe operation

APPLICATIONS

For audio frequency power amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	160	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	8	A
P _C	Collector Power Dissipation @ T _C =25°C	70	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-50~150	°C



ELECTRICAL CHARACTERISTICS**T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector- Emitter Breakdown Voltage	I _C = 50mA ; I _E = 0	100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA ; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			2	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A ; I _B = 0.5A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =160V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	30			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V		10		MHz